

<b>Notice of References Cited</b>	Application/Control No. 10/600,500		Applicant(s)/Patent Under Reexamination FAN, FRANK Y.H.	
	Examiner Andre' C. Stevenson		Art Unit 2812	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,232,787	05-2001	Lo et al.	324/751
*	B	US-6,566,897	05-2003	Lo et al.	324/751
*	C	US-6,627,884	09-2003	McCord et al.	250/306
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	K. Nakamae, H. Tanimoto, T. Takase, H. Fujioka and K. Ura. [Journal of Physics D-Applied physics, 1992, V25, N12, (December 14), pg. 1681 - 1686.] "Electron Beam Assisted High Aspect Ratio, Submicrometer Etching of passivation SiO2 on Large Scale Integra"
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.